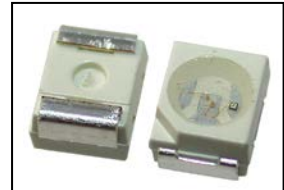




GUVV-S10SD



TECHNICAL DATA

UV-A Sensor

Features

- Indium Gallium Nitride Based Material
- Schottky-type Photodiode
- Photovoltaic Mode Operation
- High Responsivity & Low Dark Current

Applications

- UV-A Lamp Monitoring

Absolute Maximum Ratings

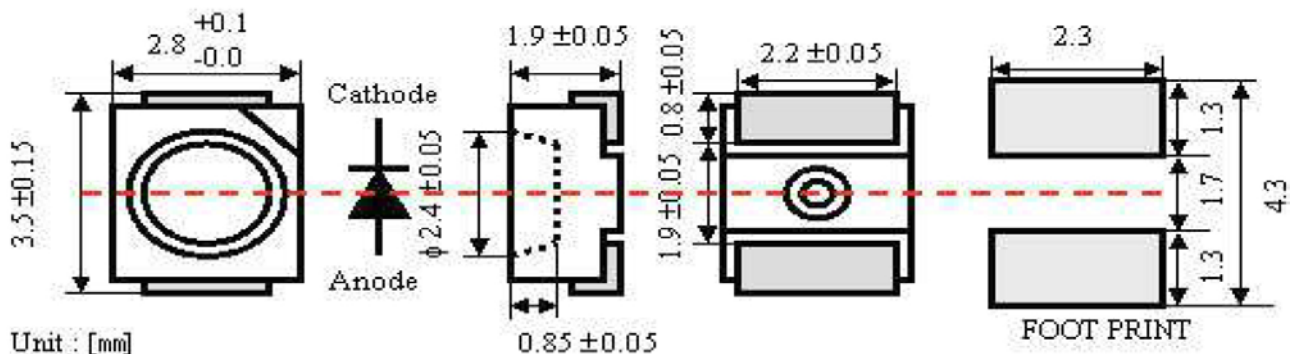
Item	Symbol	Value	Unit
Forward Current	I_F	1	mA
Reverse Voltage	V_R	2	V
Operating Temperature	T_{op}	-30 ... +85	°C
Storage Temperature	T_{st}	-40 ... +90	°C
Soldering Temperature *	T_{sol}	260	°C

* must be completed within 10 seconds

Characteristics (25°C)

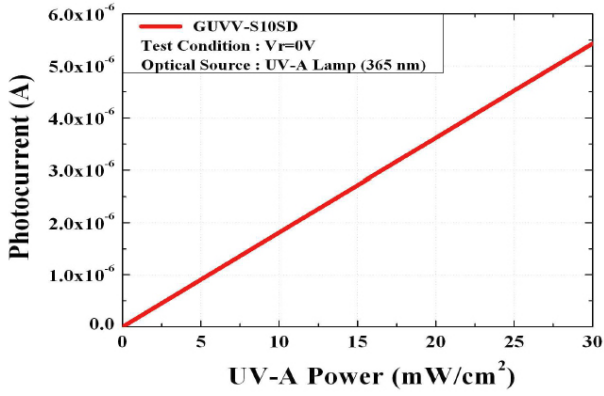
Item	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Dark Current	I_D	$V_R = 0.1 V$	-	-	1	nA
Photo Current	I_{PD}	UVA Lamp, 1 mW/cm ²	-	181	-	nA
Temperature Coefficient	I_{TC}	UVA Lamp	-	0.1	-	% / °C
Responsivity	R	$\lambda = 360 nm, V_R = 0 V$	-	0.18	-	A/W
Spectral Detection Range	λ	10% of R	240	-	395	nm

Package Dimension





Photocurrent along UV Power



Responsivity Curve

